

Evaluation of electron and hole detrapping in irradiated silicon sensors

Wednesday 30 May 2012 10:45 (20 minutes)

Preliminary results on the extraction of detrapping time constants for both electrons and holes obtained from red laser TCT measurements. Based on DLTS scans from 10-50°C the trapping levels and cross sections were obtained for highly p-irradiated silicon diodes.

Authors: Prof. BRUZZI, Mara (INFN and University of Florence); GABRYSCH, Markus (CERN)

Co-authors: DOLENC KITTELMANN, Irena (Ohio State University (US)); FERNANDEZ GARCIA, Marcos (Universidad de Cantabria (ES)); MOLL, Michael (CERN); PACIFICO, Nicola (Universite Montpellier II (FR))

Presenter: GABRYSCH, Markus (CERN)

Session Classification: Material and Defect Characterization

Track Classification: Defect and Material Characterization